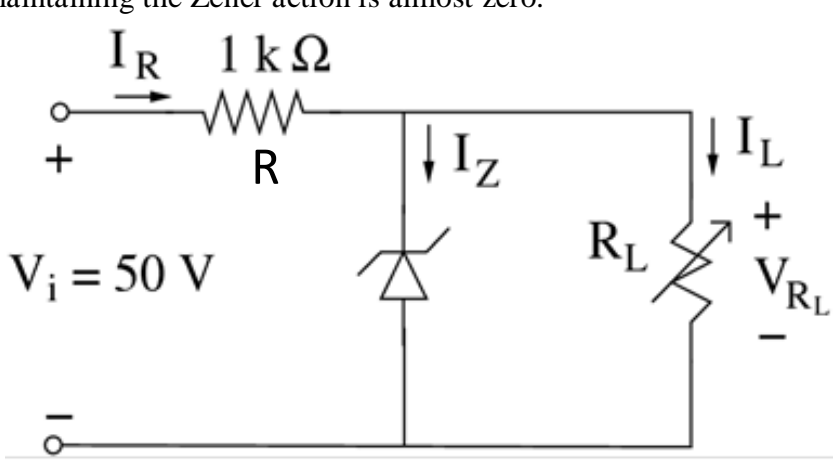
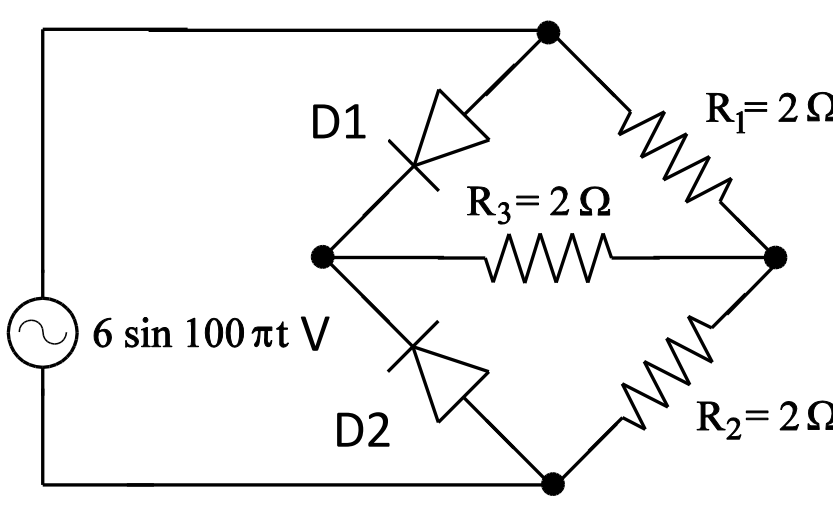


**EE101**  
**Tutorial-1 (07 Aug 2014)**

Q1.	<p>A Si diode operating at <math>27^{\circ}\text{C}</math> having the ideality factor of 1 is forward biased by a voltage of 0.8 V. If the operating temperature changes to <math>47^{\circ}\text{C}</math>, what voltage should now be applied across the diode so that the current through the diode remains constant?</p> <p>[Given that Boltzmann's constant <math>k = 1.38 \times 10^{-23} \text{ J/K}</math> and the magnitude of electronic charge <math>q = 1.6 \times 10^{-19} \text{ C}</math>]</p>
Q2.	<p>For the network shown below, determine the range of <math>R_L</math> and <math>I_L</math> that will result in the load voltage <math>V_{R_L}</math> being maintained at 10 V. The Zener diode in the circuit has a breakdown voltage of 10 V and the maximum wattage rating of 320 mW. Assume that the minimum current required for maintaining the Zener action is almost zero.</p> 
Q3.	<p>For the circuit shown below, sketch the voltage developed across the resistance <math>R_3</math> and also determine the dc voltage available at <math>R_3</math>. Assume that the diodes are ideal.</p> 

## Tutorial-1 (07 Aug 2014)

### Solutions

1. The current  $I_D$  through a diode for a forward voltage of  $V_D$  is given by

$$I_D = I_S \left\{ \exp \left( \frac{V_D}{\eta V_T} \right) - 1 \right\}$$

where  $I_S$  is the reverse saturation current,  $\eta$  is the ideality factor (given as 1), and  $V_T = \frac{kT}{q}$  is the thermal voltage at operating temperature of  $T$ .

At a forward voltage of 0.8 V and the operating temperature of 27°C (=300 K), the diode current be

$$I_D = I_S \left\{ \exp \left( \frac{0.8q}{300k} \right) - 1 \right\}$$

For the changed operating temperature of 47°C (=320 K), the reverse saturation current would be increased by a factor of 4. Now let the voltage  $V_D'$  need to be applied across diode to keep the diode current unchanged, then

$$I_D = I_S \left\{ \exp \left( \frac{0.8q}{300k} \right) - 1 \right\} = 4I_S \left\{ \exp \left( \frac{V_D'q}{320k} \right) - 1 \right\}$$

Since  $I_D \gg I_S$ ,

$$\exp \left( \frac{0.8q}{300k} \right) = 4 \exp \left( \frac{V_D'q}{320k} \right)$$

$$\frac{0.8q}{300k} = \ln 4 + \frac{V_D'q}{320k}$$

$$V_D' = \frac{320k}{q} \left( \frac{0.8q}{300k} - \ln 4 \right) = \frac{320 \times 0.8}{300} - \frac{320k}{q} \ln 4$$

$$V_D' = \frac{320 \times 0.8}{300} - \frac{320 \times 1.38 \times 10^{-23}}{1.6 \times 10^{-19}} \ln 4 = 0.8533 - 0.0383 = 0.815 \text{ V}$$

**Remark:** You will find in text book, it is mentioned that the diode forward biased characteristic shifts left with the increase in temperature, i.e., for a given voltage drop across the diode more current passes through it with increase in the temperature. Note the above solution appears to **contradict** the same. This contradiction has arisen due to the fact that the voltage drop across diode of 0.8 V taken in this problem is too large. Even with the assumption of reverse saturation current  $I_S$  of 1 pA at 27°C, for 0.8 V voltage drop the diode current turns out to be 26.7 A which is unrealistic. Actually the voltage drop across diode should have been in the range of 0.3-0.5 V. On taking the diode voltage drop at 27°C in that range, the above analysis would show that a **smaller** the voltage drop would be needed at 47°C for maintaining the same current that flows through the diode at 27°C.

2. Since  $P_Z = V_Z I_Z$ , where  $I_Z$  is the current through the Zener diode, we have

$$I_{Z_{max}} = \frac{P_{Z_{max}}}{V_Z} = \frac{320 \text{ mW}}{10 \text{ V}} = 32 \text{ mA}$$

The voltage drop across the load should be just enough to keep the Zener diode in the breakdown condition. Thus the minimum value of load resistance given by

$$R_{L_{min}} = \frac{RV_Z}{V_i - V_Z} = \frac{1 \text{ k}\Omega \times 10 \text{ V}}{50 \text{ V} - 10 \text{ V}} = 250 \Omega$$

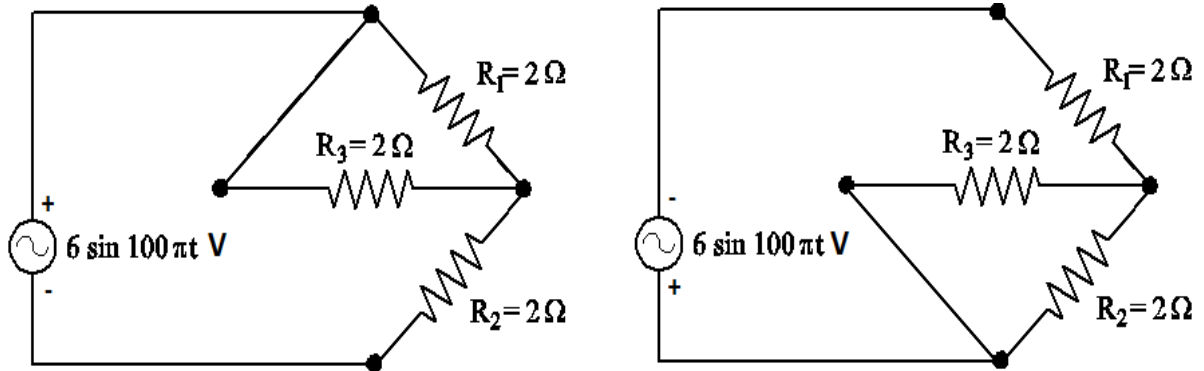
$$V_R = V_i - V_Z = 50 - 10 = 40 \text{ V}; \quad I_R = \frac{V_R}{R} = \frac{40 \text{ V}}{1 \text{ k}\Omega} = 40 \text{ mA}$$

Given that  $I_{Z_{min}} \approx 0$ , so  $I_{L_{max}} = I_R = 40 \text{ mA}$

$$I_{L_{min}} = I_R - I_{Z_{max}} = 40 - 32 = 8 \text{ mA}$$

$$R_{L_{max}} = \frac{V_Z}{I_{L_{min}}} = \frac{10 \text{ V}}{8 \text{ mA}} = 1.25 \text{ k}\Omega$$

3. For the positive and the negative cycle of the sinusoidal excitation, the given circuit reduces to as shown below,



Thus the peak value of the sinusoidal voltage drop across  $R_3$  is given by

$$(V_{R_3})_{peak} = \frac{V_m}{3} = 2 \text{ V}$$

As the direction of the current remains through  $R_3$  and therefore the voltage drop remains same for both the cycles, thus its full-wave rectified having the peak value of 2 V.

For full-wave rectified voltage across  $R_3$ , the dc value is given by

$$(V_{R_3})_{dc} = \frac{2}{\pi} (V_{R_3})_{peak} = 0.636 \times 2 = 1.272 \text{ V}$$